Ultrafast reflectivity dynamics of highly excited bulk ZnO

Tina Shih, Tobias Voss^{*} and Eric Mazur

School of Engineering & Applied Sciences - Harvard University, USA *Institute of Solid State Physics - University of Bremen, Germany



Pump-probe reflectometry

Ultrafast dielectric function dynamics

Summary

Outline

Motivation

Pump-probe reflectometry

Ultrafast dielectric function dynamics

Summary

ZnO Bandstructure



after U. Rossler, Phys. Rev. 184, 733-738 (1969)

ZnO Bandstructure



after U. Rossler, Phys. Rev. 184, 733-738 (1969)



Mazur Group

Interaction between laser light and solid materials

Mazur Group

Interaction between laser light and solid materials

Femtosecond laser pulses Semiconducting materials

Mazur Group

Interaction between laser light and solid materials

Femtosecond laser pulses Semiconducting materials

Dielectric Function





Bandstructure





Crystal Structure



Frequency Response





Bandstructure





Crystal Structure





Measured Dielectric Function

Outline

Motivation

Pump-probe reflectometry

Ultrafast dielectric function dynamics

Summary

Ti:sapphire Laser

800 nm, 50 fs 0.2 mJ







Femtosecond white light generation



Femtosecond white light generation







Delay Stage

Room temperature measurements

800-nm pump excitation

Femtosecond broadband probe

Ultrafast time resolution

Ti:sapphire Laser

Dual-angle reflectivity measurements

800 nm, 50 fs 0.2 mJ

Delay Stage

CCD Spectrometer

bulk ZnC sample



Delay Stage

Broadband dual-angle reflectometry



Delay Stage

$$\mathbf{r_p} = \frac{\epsilon \cos \theta - \sqrt{\epsilon_0} \sqrt{\epsilon - \epsilon_0 \sin^2 \theta}}{\epsilon \cos \theta + \sqrt{\epsilon_0} \sqrt{\epsilon - \epsilon_0 \sin^2 \theta}}$$
$$\mathbf{r_s} = \frac{\sqrt{\epsilon_0} \cos \theta - \sqrt{\epsilon - \epsilon_0 \sin^2 \theta}}{\sqrt{\epsilon_0} \cos \theta + \sqrt{\epsilon - \epsilon_0 \sin^2 \theta}}$$













Outline

Motivation

Pump-probe reflectometry

Ultrafast dielectric function dynamics

Summary





























Red shift of peak near 3.3 eV Bandgap renormalization



Red shift of peak near 3.3 eV Bandgap renormalization

Blue shift of valley near 3.4 eV Broadening of excitonic resonance



Red shift of peak near 3.3 eV Bandgap renormalization

Blue shift of valley near 3.4 eV Broadening of excitonic resonance

Maximum decrease of ~0.6

Damping of excitonic response



Red shift of peak near 3.3 eV Bandgap renormalization

Blue shift of valley near 3.4 eV Broadening of excitonic resonance

Maximum decrease of ~0.6

Damping of excitonic response







Above-bandgap excitation

Scattering of carriers

Filling of states

Bleaching of resonance

Decrease in absorption of ~0.7



Link to real applications





Link to real applications

High excitation pumping Excitation density of ~10¹⁶ carriers/cm³ Index changes persist over ~80 ps

Link to real applications

High excitation pumping Excitation density of ~10¹⁶ carriers/cm³ Index changes persist over ~80 ps

Determines optical length of resonators Determines lasing modes

Link to real applications

High excitation pumping Excitation density of ~10¹⁶ carriers/cm³ Index changes persist over ~80 ps

Determines optical length of resonators Determines lasing modes

Optimization of ZnO laser

Outline

Motivation

Pump-probe reflectometry

Ultrafast dielectric function dynamics

Summary

Summary

Time-Resolved ZnO Dielectric Function

Dynamics in 1-3 ps -10% change in Re(E) and Im(E) Broadening of resonance Bandgap renormalization Filling of states

Summary

Time-Resolved ZnO Dielectric Function

Dynamics in 1-3 ps ~10% change in Re(E) and Im(E) Broadening of resonance Bandgap renormalization Filling of states

Applications

Directly measure index of refraction Maximum of 12% change Large carrier excitation density Optimize design of ZnO lasers

Thanks to the members of the Mazur group

This research is supported by the National Science Foundation